

2SC2377

Silicon NPN epitaxial planar type

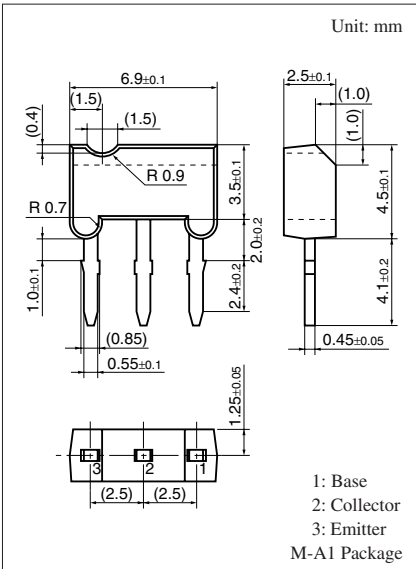
For high-frequency amplification

■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency f_T
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	30	V
Collector-emitter voltage (Base open)	V_{CEO}	20	V
Emitter-base voltage (Collector open)	V_{EBO}	3	V
Collector current	I_C	15	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



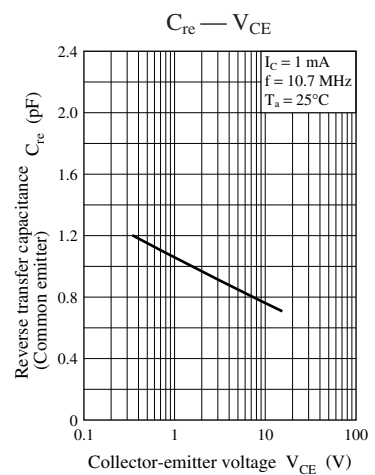
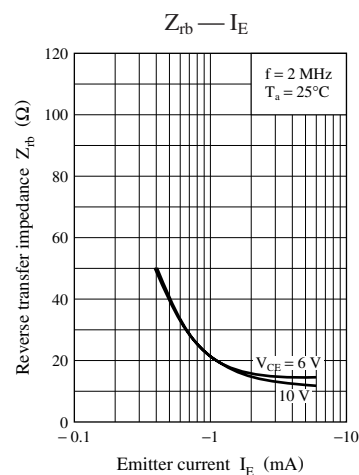
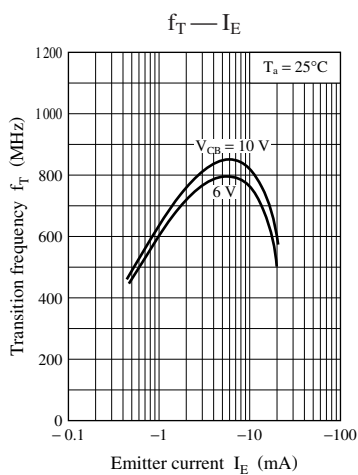
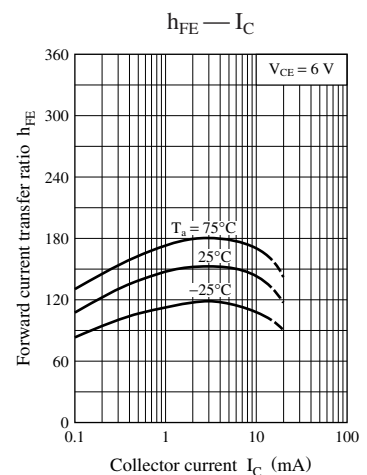
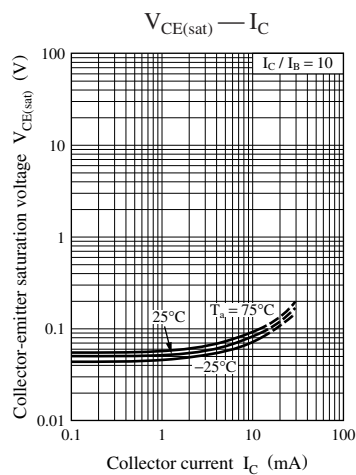
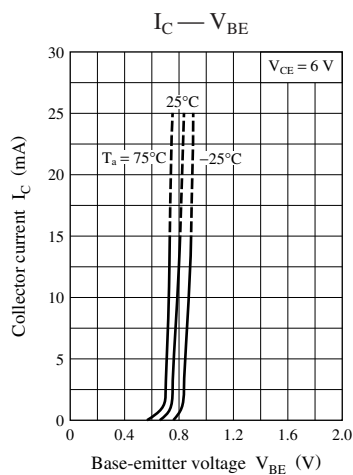
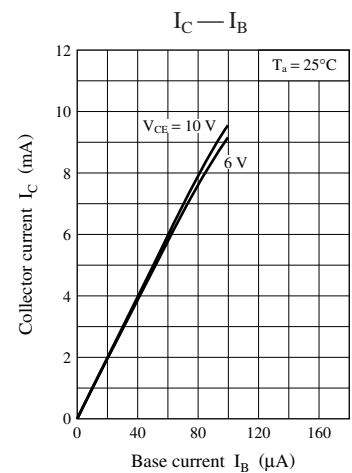
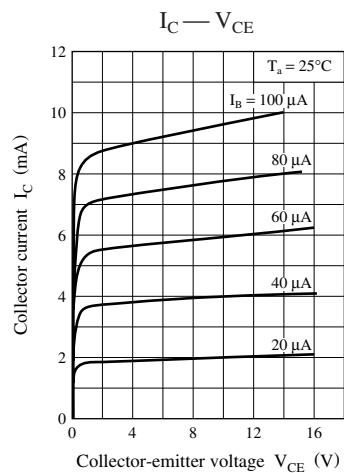
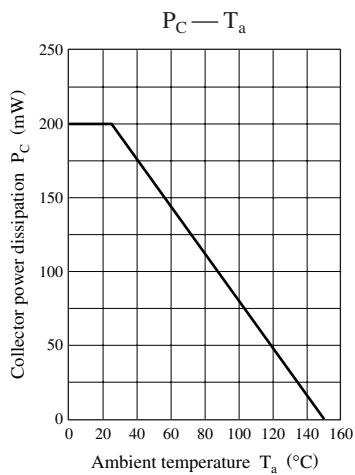
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

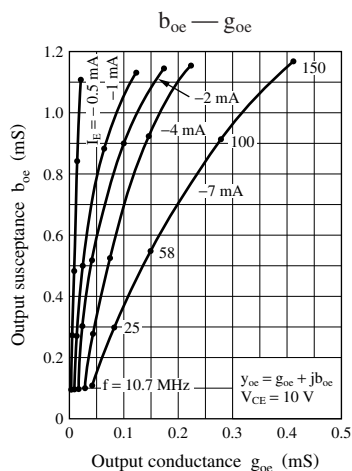
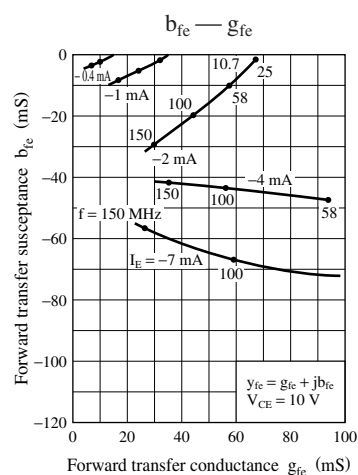
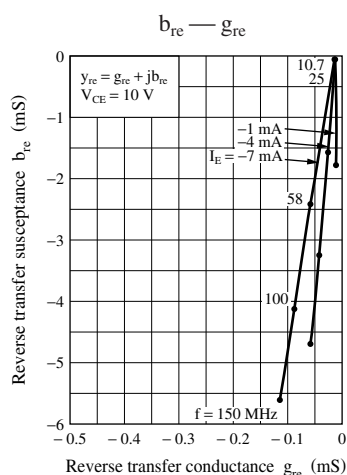
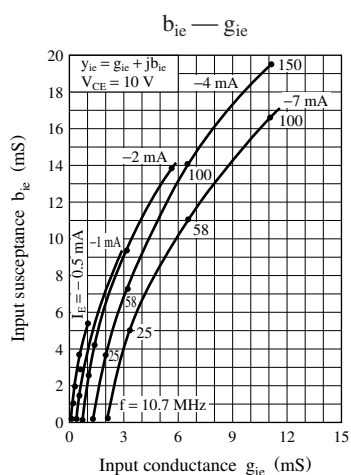
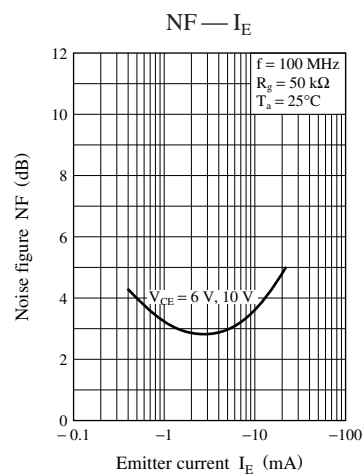
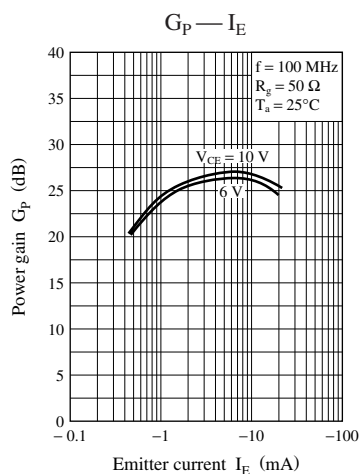
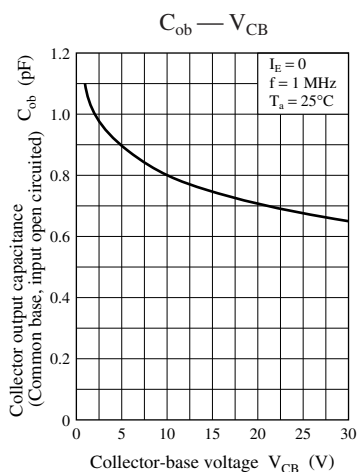
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Base-emitter voltage	V_{BE}	$V_{CB} = 6\text{ V}, I_E = -1\text{ mA}$		720		mV
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10\text{ V}, I_E = 0$			100	nA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 20\text{ V}, I_B = 0$			10	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 3\text{ V}, I_C = 0$			1	μA
Forward current transfer ratio *	h_{FE}	$V_{CB} = 6\text{ V}, I_E = -1\text{ mA}$	65		260	—
Transition frequency	f_T	$V_{CB} = 6\text{ V}, I_E = -1\text{ mA}, f = 100\text{ MHz}$	450	650		MHz
Noise figure	NF	$V_{CB} = 6\text{ V}, I_E = -1\text{ mA}, f = 100\text{ MHz}$		3.3	5.0	dB
Power gain	G_P	$V_{CB} = 6\text{ V}, I_E = -1\text{ mA}, f = 100\text{ MHz}$	20	24		dB
Reverse transfer capacitance (Common emitter)	C_{re}	$V_{CB} = 6\text{ V}, I_E = -1\text{ mA}, f = 10.7\text{ MHz}$		0.8	1.0	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	C	D
h_{FE}	65 to 160	100 to 260





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